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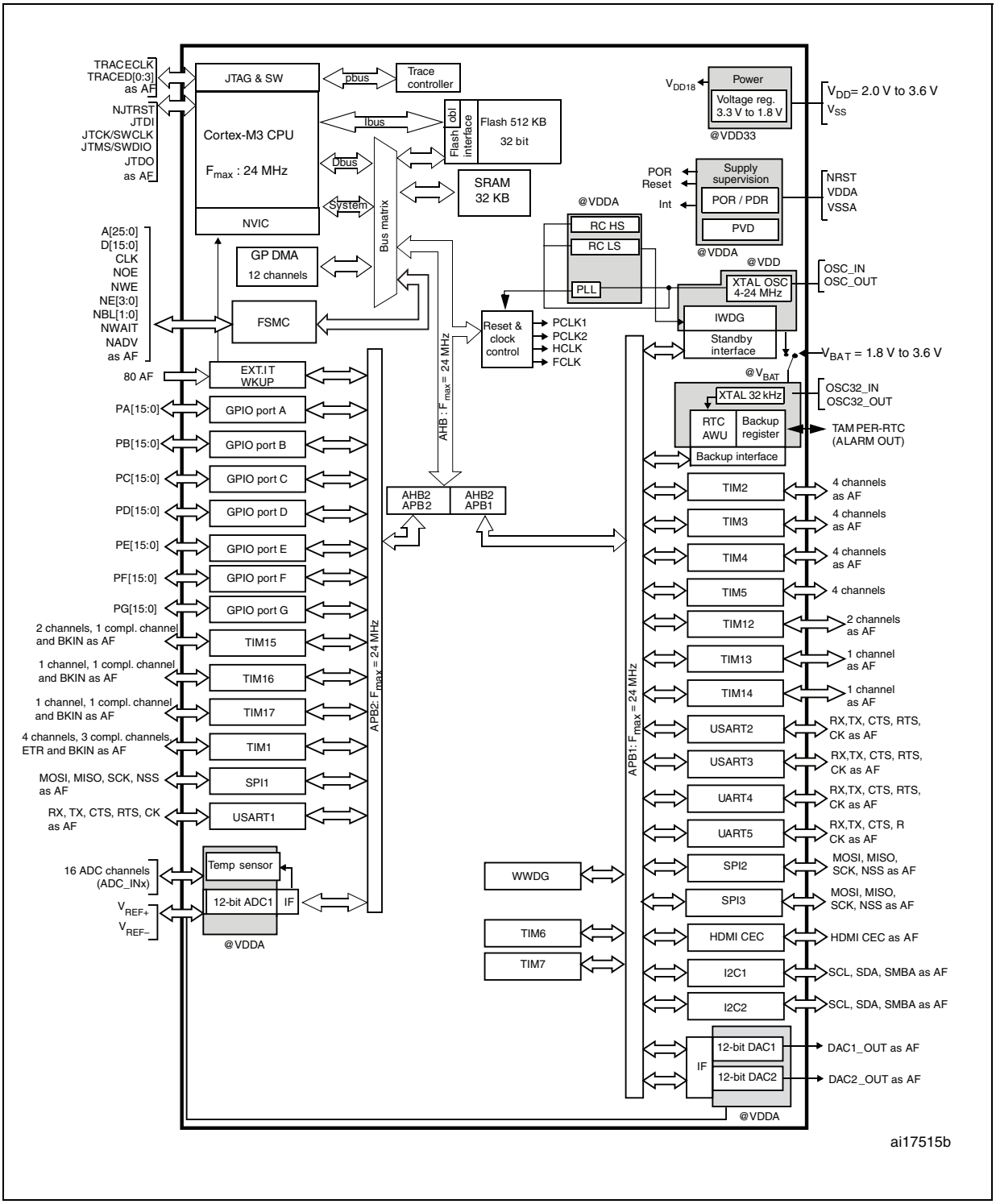
What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	80
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f100vdt7b

Figure 1. STM32F100xx value line block diagram



1. AF = alternate function on I/O port pin.
2. T_A = –40 °C to +85 °C (junction temperature up to 105 °C) or T_A = –40 °C to +105 °C (junction temperature up to 125 °C).

specific LCD interfaces. This LCD parallel interface capability makes it easy to build cost-effective graphic applications using LCD modules with embedded controllers or high-performance solutions using external controllers with dedicated acceleration.

2.2.7 Nested vectored interrupt controller (NVIC)

The STM32F100xx value line embeds a nested vectored interrupt controller able to handle up to 60 maskable interrupt channels (not including the 16 interrupt lines of Cortex®-M3) and 16 priority levels.

- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of *late arriving* higher priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

2.2.8 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 18 edge detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 112 GPIOs can be connected to the 16 external interrupt lines.

2.2.9 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-24 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example on failure of an indirectly used external crystal, resonator or oscillator).

Several prescalers allow the configuration of the AHB frequency, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the APB domains is 24 MHz.

2.2.10 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from user Flash
- Boot from system memory
- Boot from embedded SRAM

This dual digital Interface supports the following features:

- two DAC converters: one for each output channel
- up to 10-bit output
- left or right data alignment in 12-bit mode
- synchronized update capability
- noise-wave generation
- triangular-wave generation
- dual DAC channels' independent or simultaneous conversions
- DMA capability for each channel
- external triggers for conversion
- input voltage reference V_{REF+}

Eight DAC trigger inputs are used in the STM32F100xx. The DAC channels are triggered through the timer update outputs that are also connected to different DMA channels.

2.2.26 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 2 V < V_{DDA} < 3.6 V. The temperature sensor is internally connected to the ADC1_IN16 input channel which is used to convert the sensor output voltage into a digital value.

2.2.27 Serial wire JTAG debug port (SWJ-DP)

The ARM SWJ-DP Interface is embedded, and is a combined JTAG and serial wire debug port that enables either a serial wire debug or a JTAG probe to be connected to the target. The JTAG TMS and TCK pins are shared respectively with SWDIO and SWCLK and a specific sequence on the TMS pin is used to switch between JTAG-DP and SW-DP.

Figure 7. Pin loading conditions

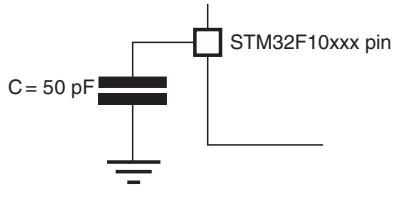
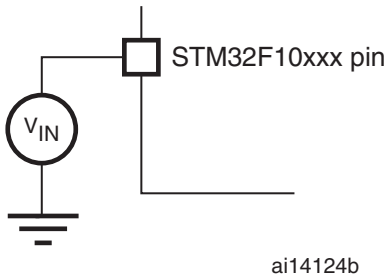
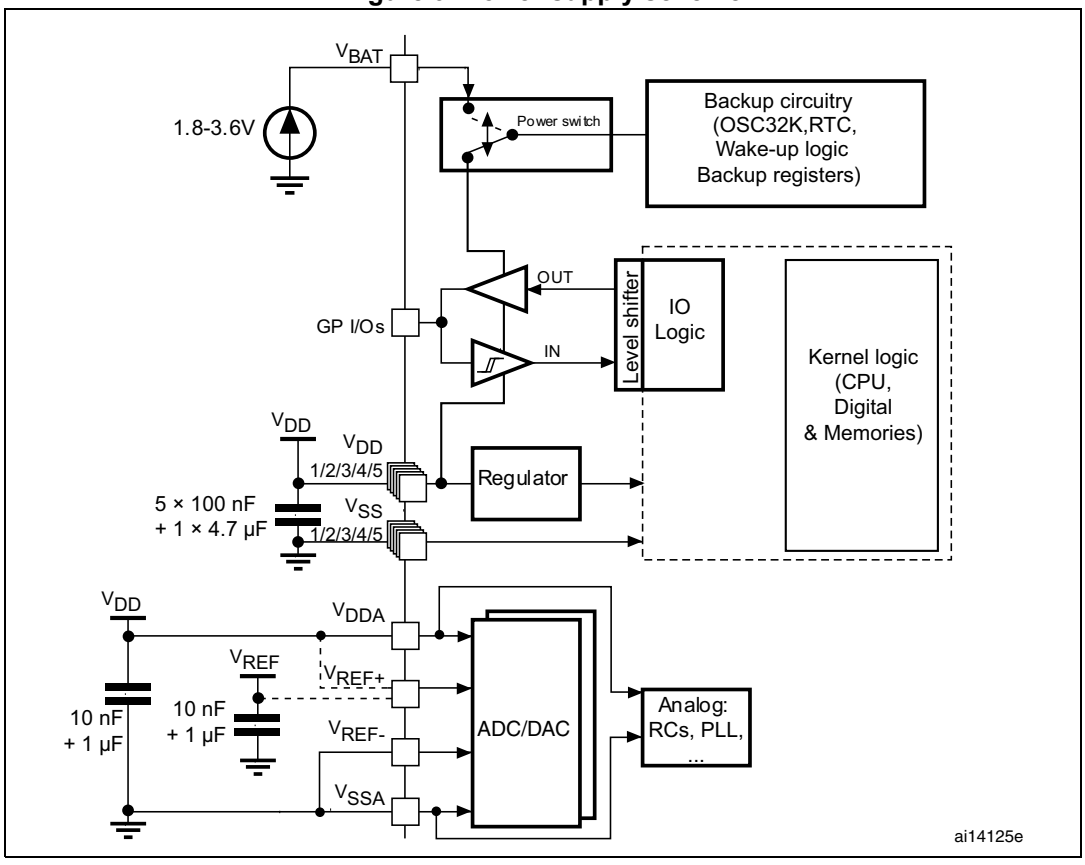


Figure 8. Pin input voltage



5.1.6 Power supply scheme

Figure 9. Power supply scheme



Caution: In *Figure 9*, the 4.7 µF capacitor must be connected to V_{DD3}.

5.3.4 Embedded reference voltage

The parameters given in *Table 12* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

Table 12. Embedded internal reference voltage

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{REFINT}	Internal reference voltage	–40 °C < T_A < +105 °C	1.16	1.20	1.26	V
		–40 °C < T_A < +85 °C	1.16	1.20	1.24	V
$T_{S\_vrefint}$(1)	ADC sampling time when reading the internal reference voltage	-	-	5.1	17.1(2)	µs
V_{RERINT}(2)	Internal reference voltage spread over the temperature range	V_{DD} = 3 V ±10 mV	-	-	10	mV
T_{Coeff}(2)	Temperature coefficient	-	-	-	100	ppm/°C

1. Shortest sampling time can be determined in the application by multiple iterations.
2. Guaranteed by design, not tested in production.

5.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.
The current consumption is measured as described in *Figure 10: Current consumption measurement scheme*.
All Run-mode current consumption measurements given in this section are performed with a reduced code that gives a consumption equivalent to Dhrystone 2.1 code.

Maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except if it is explicitly mentioned
- Prefetch in on (reminder: this bit must be set before clock setting and bus prescaling)
- When the peripherals are enabled $f_{PCLK1} = f_{HCLK}/2$, $f_{PCLK2} = f_{HCLK}$

The parameters given in *Table 13* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

Table 15. STM32F100xxB maximum current consumption in Sleep mode, code running from Flash or RAM

Symbol	Parameter	Conditions	f_{HCLK}	Max(1)		Unit
				T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Sleep mode	External clock(2) all peripherals enabled	24 MHz	14.1	14.3	mA
			16 MHz	9.7	10.3	
			8 MHz	5.9	6.2	
		External clock(2), all peripherals disabled	24 MHz	4.2	4.6	
			16 MHz	3.7	4.1	
			8 MHz	2.9	3.4	
		HSI clock(2), all peripherals enabled	24 MHz	12.5	12.7	
			16 MHz	8.2	8.5	
			8 MHz	6.4	6.6	
		HSI clock(2), all peripherals disabled	24 MHz	2.3	2.5	
			16 MHz	1.7	2	
			8 MHz	1.4	1.7	

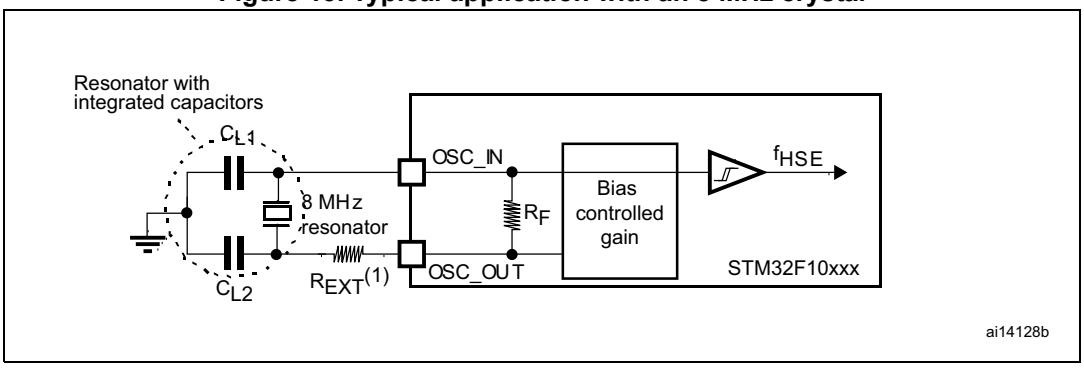
1. Based on characterization, tested in production at V_{DD} max and f_{HCLK} max with peripherals enabled.
2. External clock or HSI frequency is 8 MHz and PLL is on when f_{HCLK} > 8 MHz.

Table 22. HSE 4-24 MHz oscillator characteristics(1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
C_{L1} C_{L2}(3)	Recommended load capacitance versus equivalent serial resistance of the crystal (R_S)(4)	R_S = 30 Ω	-	30	-	pF
i_2	HSE driving current	V_{DD} = 3.3 V V_{IN} = V_{SS} with 30 pF load	-	-	1	mA
g_m	Oscillator transconductance	Startup	25	-	-	mA/V
$t_{SU(HSE)}$(5)	Startup time	V_{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
2. Based on characterization, not tested in production.
3. It is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2}, are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.
4. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
5. $t_{SU(HSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

Figure 13. Typical application with an 8 MHz crystal



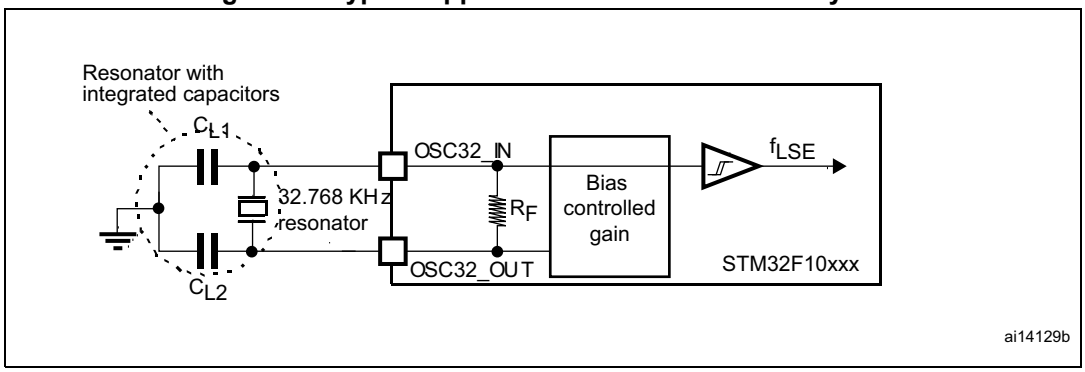
1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 23*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Note: For C_{L1} and C_{L2} it is recommended to use high-quality ceramic capacitors in the 5 pF to 15 pF range selected to match the requirements of the crystal or resonator. C_{L1} and C_{L2}, are usually the same size. The crystal manufacturer typically specifies a load capacitance which

Figure 14. Typical application with a 32.768 kHz crystal



5.3.7 Internal clock source characteristics

The parameters given in *Table 24* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 9*.

High-speed internal (HSI) RC oscillator

Table 24. HSI oscillator characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSI}	Frequency	-	-	8	-	MHz
ACC_{HSI}	Accuracy of HSI oscillator	T_A = –40 to 105 °C(2)	-2.4	-	2.5	%
		T_A = –10 to 85 °C(2)	-2.2	-	1.3	%
		T_A = 0 to 70 °C(2)	-1.9	-	1.3	%
		T_A = 25 °C	-1	-	1	%
$t_{su(HSI)}$(3)	HSI oscillator startup time	-	1	-	2	µs
$I_{DD(HSI)}$(3)	HSI oscillator power consumption	-	-	80	100	µA

1. V_{DD} = 3.3 V, T_A = –40 to 105 °C °C unless otherwise specified.
2. Based on characterization, not tested in production.
3. Guaranteed by design. Not tested in production

Low-speed internal (LSI) RC oscillator

Table 25. LSI oscillator characteristics (1)

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}	Frequency	30	40	60	kHz
$t_{su(LSI)}$(2)	LSI oscillator startup time	-	-	85	µs
$I_{DD(LSI)}$(2)	LSI oscillator power consumption	-	0.65	1.2	µA

1. V_{DD} = 3 V, T_A = –40 to 105 °C °C unless otherwise specified.
2. Guaranteed by design, not tested in production.

Table 30. Asynchronous non-multiplexed SRAM/PSRAM/NOR read timings(1) (2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$5T_{HCLK} – 1.5$	$5T_{HCLK} + 2$	ns
$t_{v(NOE\_NE)}$	FSMC_NEx low to FSMC_NOE low	0.5	1.5	ns
$t_{w(NOE)}$	FSMC_NOE low time	$5T_{HCLK} – 1.5$	$5T_{HCLK} + 1.5$	ns
$t_{h(NE\_NOE)}$	FSMC_NOE high to FSMC_NE high hold time	–1.5	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	0	ns
$t_{h(A\_NOE)}$	Address hold time after FSMC_NOE high	0.1	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	0	ns
$t_{h(BL\_NOE)}$	FSMC_BL hold time after FSMC_NOE high	0	-	ns
$t_{su(Data\_NE)}$	Data to FSMC_NEx high setup time	$2T_{HCLK} + 25$	-	ns
$t_{su(Data\_NOE)}$	Data to FSMC_NOEx high setup time	$2T_{HCLK} + 25$	-	ns
$t_{h(Data\_NOE)}$	Data hold time after FSMC_NOE high	0	-	ns
$t_{h(Data\_NE)}$	Data hold time after FSMC_NEx high	0	-	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	-	5	ns
$t_{w(NADV)}$	FSMC_NADV low time	-	$T_{HCLK} + 1.5$	ns

1. C_L = 15 pF.
2. Preliminary values.

Table 34. Synchronous multiplexed NOR/PSRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	27.7	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x = 0...2)	-	1.5	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x = 0...2)	2	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	4	ns
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	5	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x = 16...25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x = 16...25)	2	-	ns
$t_{d(CLKH-NOEL)}$	FSMC_CLK high to FSMC_NOE low	-	1	ns
$t_{d(CLKL-NOEH)}$	FSMC_CLK low to FSMC_NOE high	0.5	-	ns
$t_{d(CLKL-ADV)}$	FSMC_CLK low to FSMC_AD[15:0] valid	-	12	ns
$t_{d(CLKL-ADIV)}$	FSMC_CLK low to FSMC_AD[15:0] invalid	0	-	ns
$t_{su(ADV-CLKH)}$	FSMC_A/D[15:0] valid data before FSMC_CLK high	6	-	ns
$t_{h(CLKH-ADV)}$	FSMC_A/D[15:0] valid data after FSMC_CLK high	0	-	ns
$t_{su(NWAITV-CLKH)}$	FSMC_NWAIT valid before FSMC_CLK high	8	-	ns
$t_{h(CLKH-NWAITV)}$	FSMC_NWAIT valid after FSMC_CLK high	2	-	ns

1. C_L = 15 pF.
2. Preliminary values.

Figure 21. Synchronous non-multiplexed NOR/PSRAM read timings

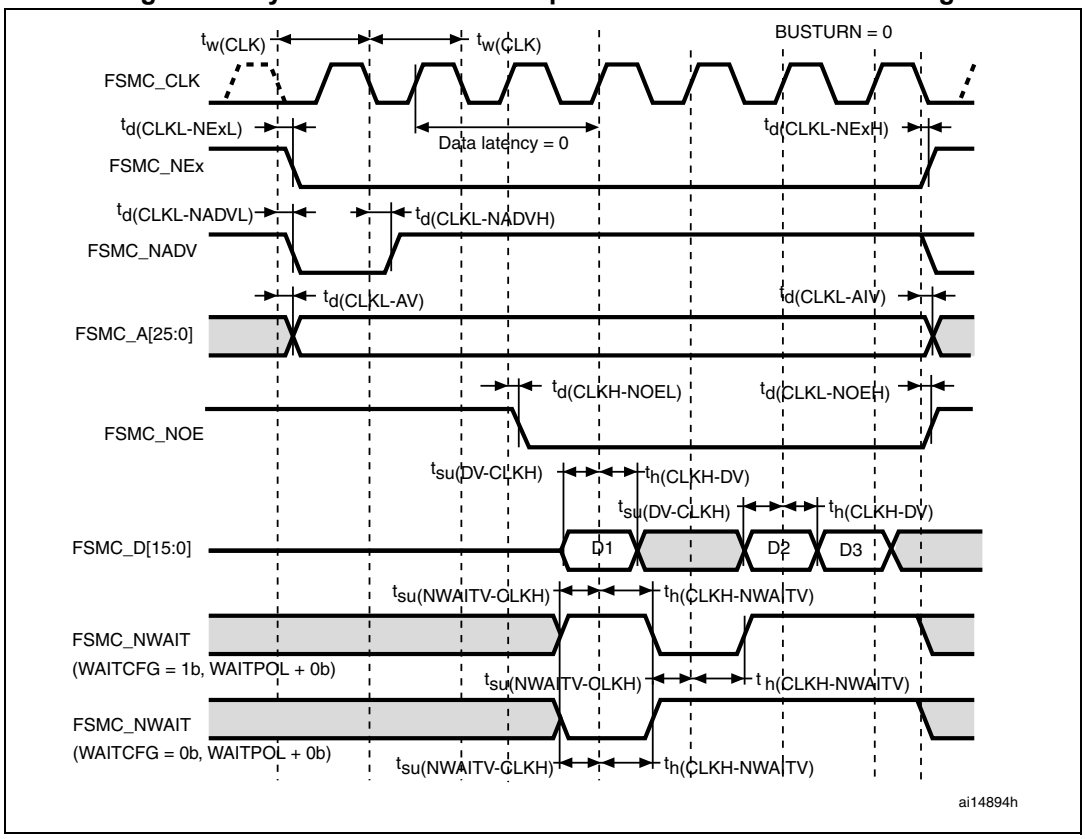


Table 36. Synchronous non-multiplexed NOR/PSRAM read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(CLK)}$	FSMC_CLK period	27.7	-	ns
$t_{d(CLKL-NExL)}$	FSMC_CLK low to FSMC_NEx low (x = 0...2)	-	1.5	ns
$t_{d(CLKL-NExH)}$	FSMC_CLK low to FSMC_NEx high (x = 0...2)	2	-	ns
$t_{d(CLKL-NADVL)}$	FSMC_CLK low to FSMC_NADV low	-	4	ns
$t_{d(CLKL-NADVH)}$	FSMC_CLK low to FSMC_NADV high	5	-	ns
$t_{d(CLKL-AV)}$	FSMC_CLK low to FSMC_Ax valid (x = 0...25)	-	0	ns
$t_{d(CLKL-AIV)}$	FSMC_CLK low to FSMC_Ax invalid (x = 0...25)	4	-	ns
$t_{d(CLKH-NOEL)}$	FSMC_CLK high to FSMC_NOE low	-	1.5	ns
$t_{d(CLKL-NOEH)}$	FSMC_CLK low to FSMC_NOE high	1.5	-	ns
$t_{su(DV-CLKH)}$	FSMC_D[15:0] valid data before FSMC_CLK high	6.5	-	ns
$t_{h(CLKH-DV)}$	FSMC_D[15:0] valid data after FSMC_CLK high	7	-	ns
$t_{su(NWAITV-CLKH)}$	FSMC_NWAIT valid before FSMC_SMCLK high	7	-	ns
$t_{h(CLKH-NWAITV)}$	FSMC_NWAIT valid after FSMC_CLK high	2	-	ns

1. C_L = 15 pF.
2. Preliminary values.

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device is monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Table 39. EMI characteristics

Symbol	Parameter	Conditions	Monitored frequency band	Max vs. [f_{HSE}/f_{HCLK}]	Unit
				8/24 MHz	
S_{EMI}	Peak level	V_{DD} = 3.6 V, T_A = 25°C, LQFP144 package compliant with SAE J1752/3	0.1 MHz to 30 MHz	16	dBµV
			30 MHz to 130 MHz	25	
			130 MHz to 1GHz	25	
			SAE EMI Level	4	-

5.3.12 Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.

Table 40. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	T_A = +25 °C conforming to JESD22-A114	2	2000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (charge device model)	T_A = +25 °C conforming to JESD22-C101	II	500	

1. Based on characterization results, not tested in production.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

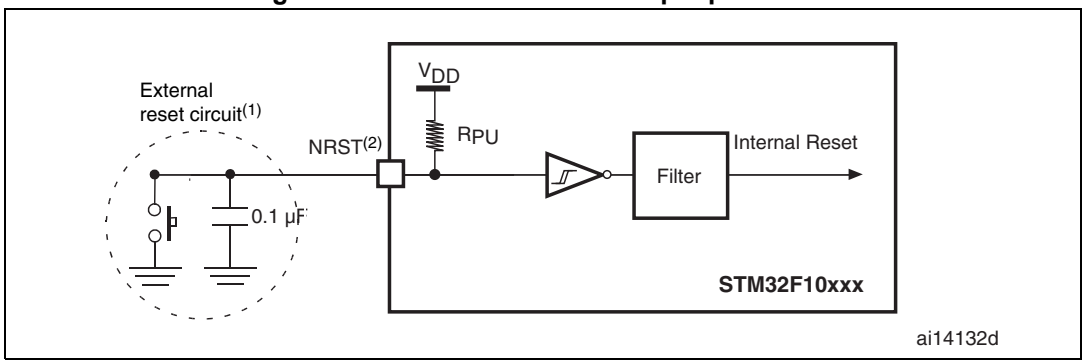
- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD78 IC latch-up standard.

Table 41. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = +105 °C conforming to JESD78	II level A

Figure 28. Recommended NRST pin protection



1. The reset network protects the device against parasitic resets.
2. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max level specified in *Table 46*. Otherwise the reset will not be taken into account by the device.

Table 52. R_{AIN} max for f_{ADC} = 12 MHz(1)

T_s (cycles)	t_S (µs)	R_{AIN} max (kΩ)
1.5	0.125	0.4
7.5	0.625	5.9
13.5	1.125	11.4
28.5	2.375	25.2
41.5	3.45	37.2
55.5	4.625	50
71.5	5.96	NA
239.5	20	NA

1. Guaranteed by design, not tested in production.

Table 53. ADC accuracy - limited test conditions(1)(2)

Symbol	Parameter	Test conditions	Typ	Max	Unit
ET	Total unadjusted error	f_{PCLK2} = 24 MHz, f_{ADC} = 12 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 3 V to 3.6 V V_{REF+} = V_{DDA} T_A = 25 °C Measurements made after ADC calibration	±1.5	±2.5	LSB
EO	Offset error		±1	±2	
EG	Gain error		±0.5	±1.5	
ED	Differential linearity error		±1.5	±2	
EL	Integral linearity error		±1.5	±2	

1. ADC DC accuracy values are measured after internal calibration.
2. Preliminary values.

Table 54. ADC accuracy(1) (2) (3)

Symbol	Parameter	Test conditions	Typ	Max	Unit
ET	Total unadjusted error	f_{PCLK2} = 24 MHz, f_{ADC} = 12 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 2.4 V to 3.6 V T_A = Full operating range Measurements made after ADC calibration	±2	±5	LSB
EO	Offset error		±1.5	±2.5	
EG	Gain error		±1.5	±3	
ED	Differential linearity error		±1.5	±2.5	
EL	Integral linearity error		±1.5	±4.5	

1. ADC DC accuracy values are measured after internal calibration.
2. Better performance could be achieved in restricted V_{DD}, frequency, V_{REF} and temperature ranges.
3. Preliminary values.

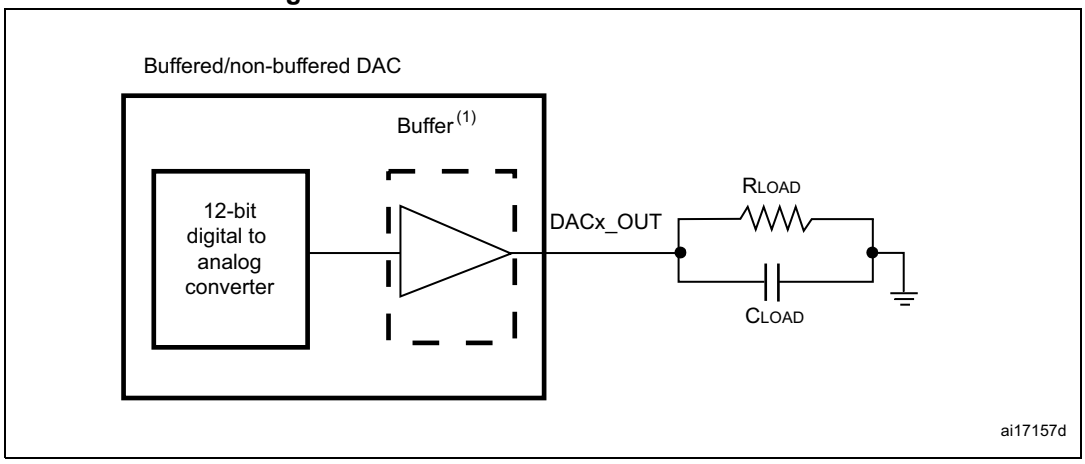
Note: ADC accuracy vs. negative injection current: Injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.

Table 55. DAC characteristics (continued)

Symbol	Parameter	Min	Typ	Max(1)	Unit	Comments
Offset(1)	Offset error (difference between measured value at Code (0x800) and the ideal value = $V_{REF+}/2$)	-	-	±10	mV	Given for the DAC in 12-bit configuration
		-	-	±3	LSB	Given for the DAC in 10-bit at V_{REF+} = 3.6 V
		-	-	±12	LSB	Given for the DAC in 12-bit at V_{REF+} = 3.6 V
Gain error(1)	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration
$t_{SETTLING}$(1)	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±1LSB	-	3	4	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
Update rate(1)	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
t_{WAKEUP}(1)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ input code between lowest and highest possible ones.
PSRR+ (1)	Power supply rejection ratio (to V_{DDA}) (static DC measurement	-	–67	–40	dB	No R_{LOAD}, C_{LOAD} = 50 pF

1. Preliminary values.
2. Quiescent mode refer to the state of the DAC keeping steady value on the output, so no dynamic consumption is involved.

Figure 37. 12-bit buffered /non-buffered DAC



1. The DAC integrates an output buffer that can be used to reduce the output impedance and to drive external loads directly without the use of an external operational amplifier. The buffer can be bypassed by configuring the BOFFx bit in the DAC_CR register.

5.3.20 Temperature sensor characteristics

Table 56. TS characteristics

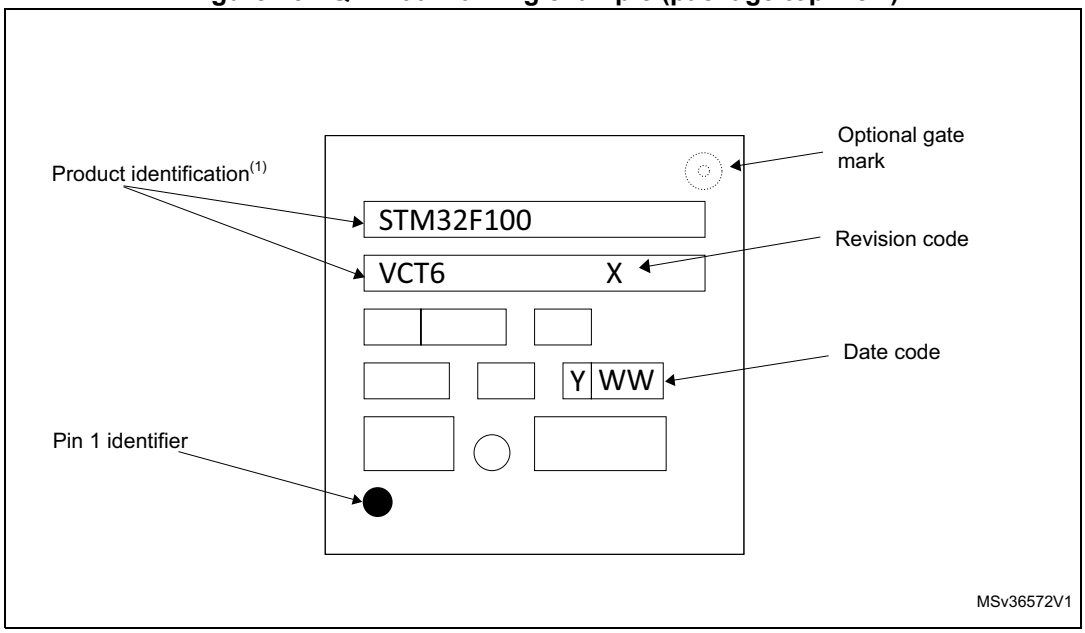
Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	4.0	4.3	4.6	mV/°C
V_{25}(1)	Voltage at 25°C	1.32	1.41	1.50	V
t_{START}(2)	Startup time	4	-	10	µs
T_{S_temp}(3)(2)	ADC sampling time when reading the temperature	-	-	17.1	µs

1. Guaranteed by characterization, not tested in production.
2. Guaranteed by design, not tested in production.
3. Shortest sampling time can be determined in the application by multiple iterations.

Device marking for LQFP100

The following figure shows the device marking for the LQFP100 package.

Figure 43.LQFP100 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

6.5 Thermal characteristics

The maximum chip junction temperature ($T_J$max) must never exceed the values given in *Table 9: General operating conditions on page 38*.

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

T_J max = T_A max + (P_D max x Θ_{JA})

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$$P_{I/O} \text{ max} = \Sigma (V_{OL} \times I_{OL}) + \Sigma((V_{DD} - V_{OH}) \times I_{OH}),$$

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 60. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP 144 - 20 × 20 mm / 0.5 mm pitch	35	°C/W
	Thermal resistance junction-ambient LQFP 100 - 14 × 14 mm / 0.5 mm pitch	40	
	Thermal resistance junction-ambient LQFP 64 - 10 × 10 mm / 0.5 mm pitch	49	

6.5.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

7 Ordering information scheme

Table 61. Ordering information scheme

Example: STM32 F 100 V C T 6 B xxx

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

F = General-purpose

Device subfamily

100 = value line

Pin count

R = 64 pins

V = 100 pins

Z = 144 pins

Flash memory size

C = 256 Kbytes of Flash memory

D = 384 Kbytes of Flash memory

E = 512 Kbytes of Flash memory

Package

T = LQFP

Temperature range

6 = Industrial temperature range, –40 to 85 °C

7 = Industrial temperature range, –40 to 105 °C

Internal code

B

Options

xxx = programmed parts

TR = tape and real

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact your nearest ST sales office.